# 2SB0968 (2SB968)

# Silicon PNP epitaxial planar type

For low-frequency output amplification Complementary to 2SD1295

#### ■ Features

- Possible to solder radiation fin directly to printed circuit board
- High collector-emitter voltage (Base open) V<sub>CEO</sub>
- Large collector power dissipation P<sub>C</sub>

### ■ Absolute Maximum Ratings $T_a = 25^{\circ}C$

Parameter	Symbol	Rating	Unit	
Collector-base voltage (Emitter open)	$V_{CBO}$	-50	V	
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	-40	V	
Emitter-base voltage (Collector open)	$V_{EBO}$	-5	V	
Collector current	$I_{C}$	-1.5	A	
Peak collector current	$I_{CP}$	-3	A	
Collector power dissipation ( $T_C = 25^{\circ}C$ )	P <sub>C</sub>	10	W	
Junction temperature	Tj	150	°C	
Storage temperature	T <sub>stg</sub>	-55 to +150	°C	

#### ■ Package

- Code
- U-G2
- Pin Name
  - 1: Base
  - 2: Collector
  - 3: Emitter

### ■ Electrical Characteristics T<sub>a</sub> = 25°C ± 3°C

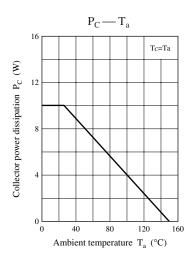
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	$V_{CBO}$	$I_C = -1 \text{ mA}, I_E = 0$	-50			V
Collector-emitter voltage (Base open)	$V_{CEO}$	$I_{\rm C} = -2 \text{ mA}, I_{\rm B} = 0$	-40			V
Collector-base cutoff current (Emitter open)	$I_{CBO}$	$V_{CB} = -20 \text{ V}, I_E = 0$			-1	μΑ
Collector-emitter cutoff current (Base open)	I <sub>CEO</sub>	$V_{CE} = -10 \text{ V}, I_B = 0$			-100	μΑ
Emitter-base cutoff current (Collector open)	$I_{EBO}$	$V_{EB} = -5 \text{ V}, I_C = 0$			-10	μΑ
Forward current transfer ratio	h <sub>FE1</sub> *	$V_{CE} = -5 \text{ V}, I_{C} = -1 \text{ A}$	80		220	_
	h <sub>FE2</sub>	$V_{CE} = -5 \text{ V}, I_{C} = -1 \text{ mA}$	10			
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	$I_C = -1.5 \text{ A}, I_B = -0.15 \text{ A}$			-1	V
Base-emitter saturation voltage	V <sub>BE(sat)</sub>	$I_C = -2 A, I_B = -0.2 A$			-1.5	V
Transition frequency	$f_T$	$V_{CE} = -5 \text{ V}, I_{C} = -0.5 \text{ A}, f = 200 \text{ MHz}$		150		MHz
Collector output capacitance	C <sub>ob</sub>	$V_{CB} = -20 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		45		pF
(Common base, input open circuited)						

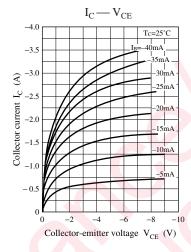
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

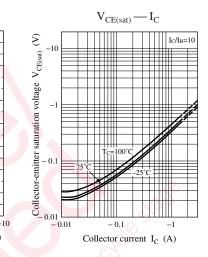
#### 2. \*: Rank classification

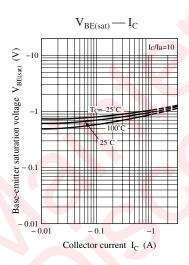
Rank	Q	R
$h_{\rm FE1}$	80 to 160	120 to 220

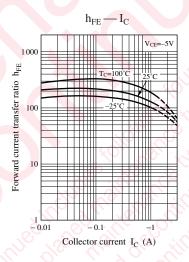
Note) The part number in the parenthesis shows conventional part number.

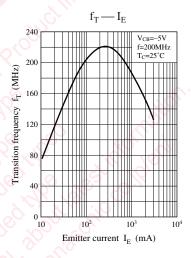


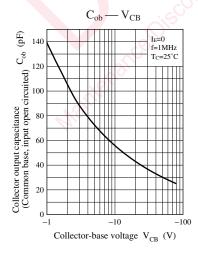


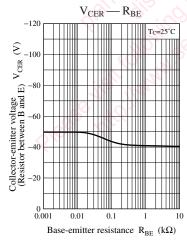


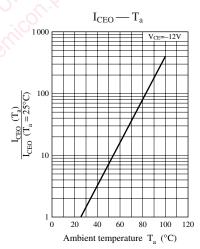




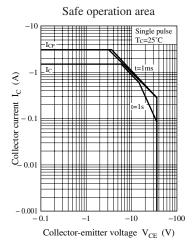




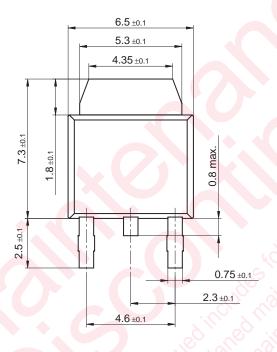




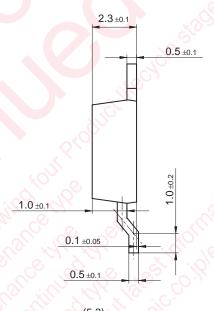
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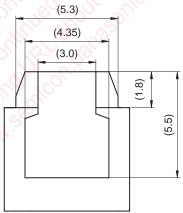


U-G2 Unit: mm









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